

7.3 Plasma Sources

Classification of plasma sources:

according to pressure

- low pressure
- atmospheric pressure

importance of mean free path:

$$\lambda = 1 / n\sigma$$

n – density, σ – collision frequency

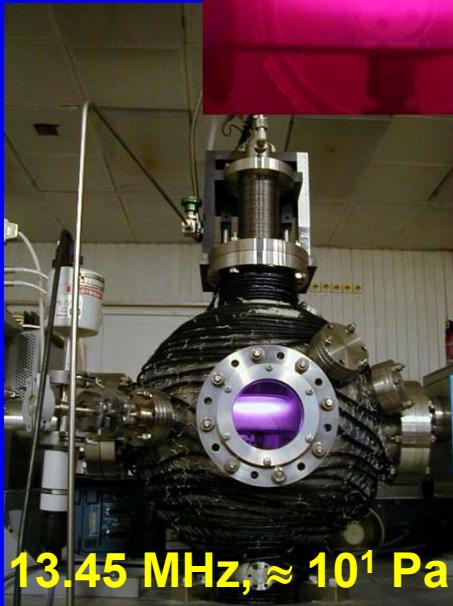
according to excitation frequency

- d.c. (d.c. glow discharge or planar diode, thermionically supported diode, d.c. magnetron, vacuum arc)
- audio frequencies (50 Hz up to 30 kHz)
- low radio frequencies (30 kHz – 1 MHz)
- high radio frequencies (usually 1 – 60 MHz, typically 13.56MHz, 27.12MHz)
- microwave frequency (typically 2.45 GHz)

importance of electron and ion plasma frequencies:

$$\omega_{pe,i} = \sqrt{\frac{e^2 n_e}{\epsilon_0 m_{e,i}}},$$

Laboratory plasma sources (DPE MU Brno)



capacitively
coupled RF
discharge



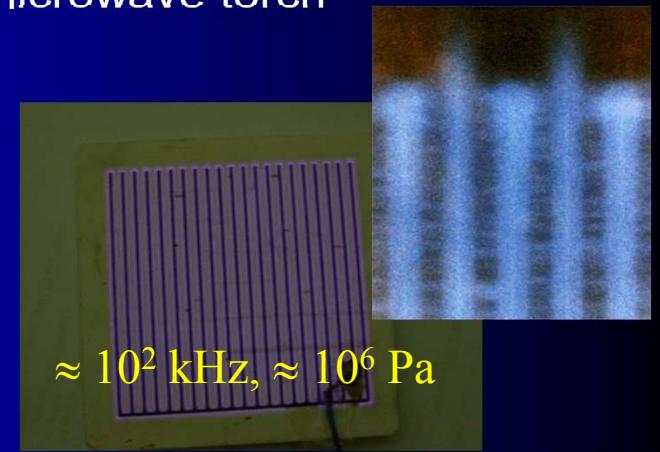
microwave resonator
discharge (AsTeX)



inductively coupled
RF discharge



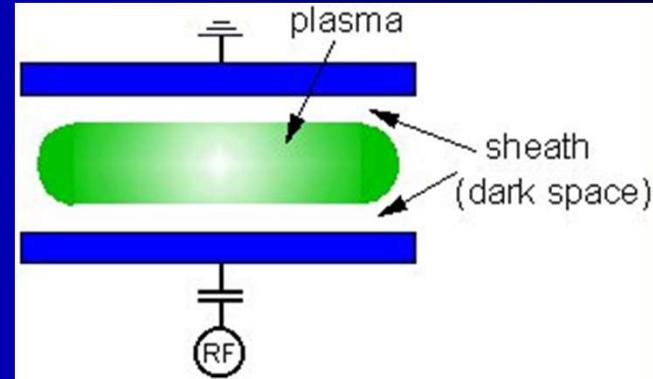
2.45 GHz, $\approx 10^6$ Pa
microwave torch



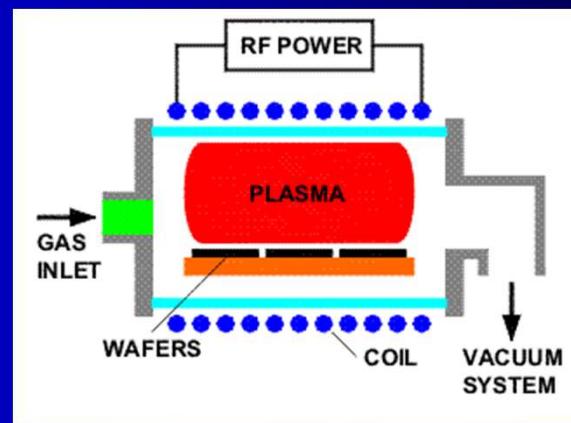
coplanar barrier discharge
at atmospheric pressure

7.3.1 Typical Low Pressure, High Frequency Plasma Sources

- radio frequency capacitively coupled plasma (CCP)



- r.f. inductively coupled plasma (ICP)

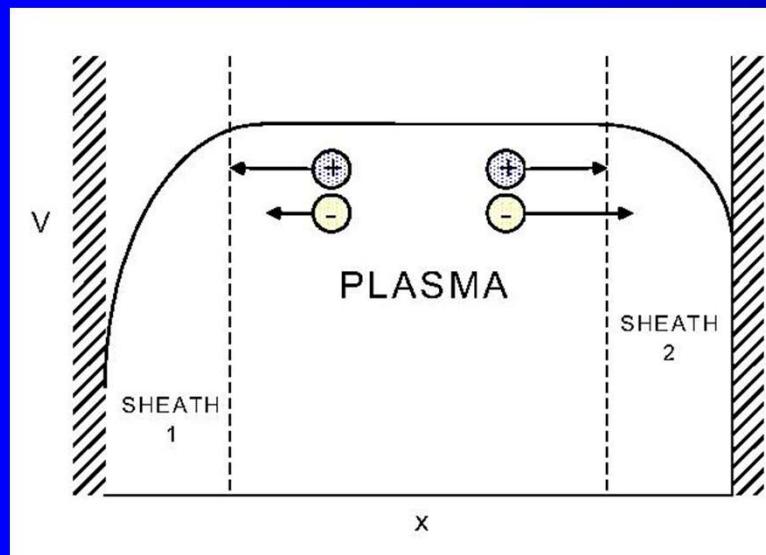


- plasma sustained by electromagnetic wave: electron cyclotron resonance, helicon discharge, surface wave discharge

Principle of r.f. CCP discharges

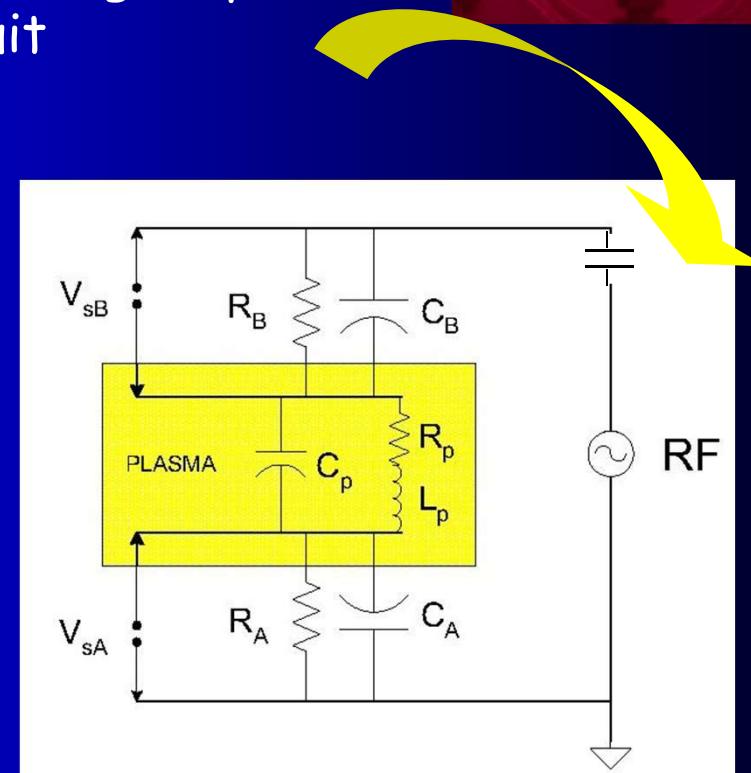
discharge is sustained by r.f. current and voltage coupled via capacitive plasma sheath

electrical circuit usually contains „blocking“ capacitor
☞ dc current cannot flow in the circuit



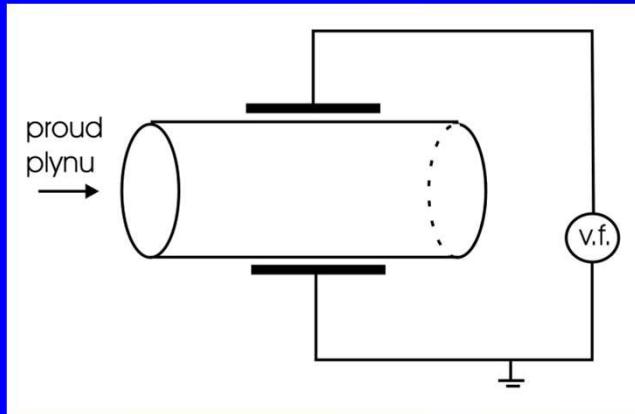
$$\frac{V_{sB}}{V_{sA}} \approx \left(\frac{A_A}{A_B} \right)^q$$

voltage divider action due to displacement current in plasma sheaths

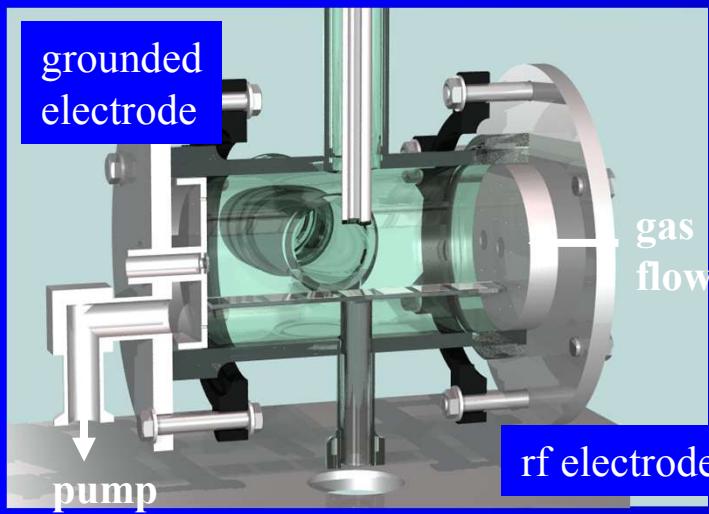


Construction of CCP reactors

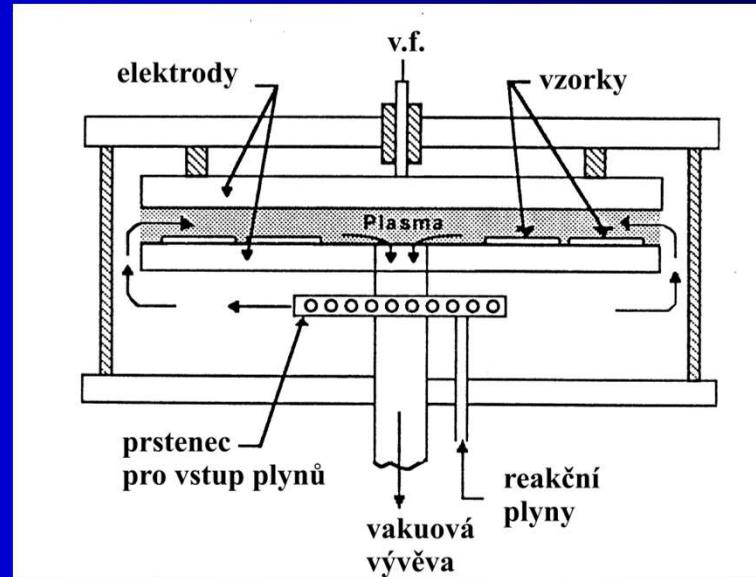
- horizontal reactor
 - with outer electrodes



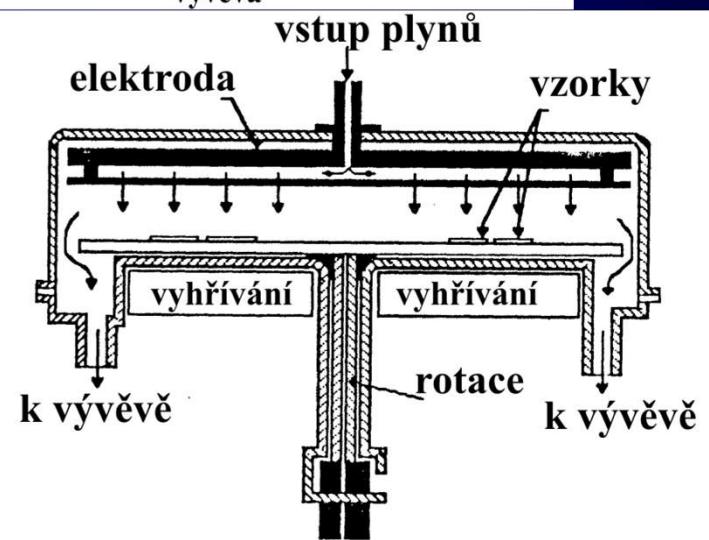
- with inner electrodes



- vertical reactor with inner parallel electrodes (parallel-plate diode discharge)

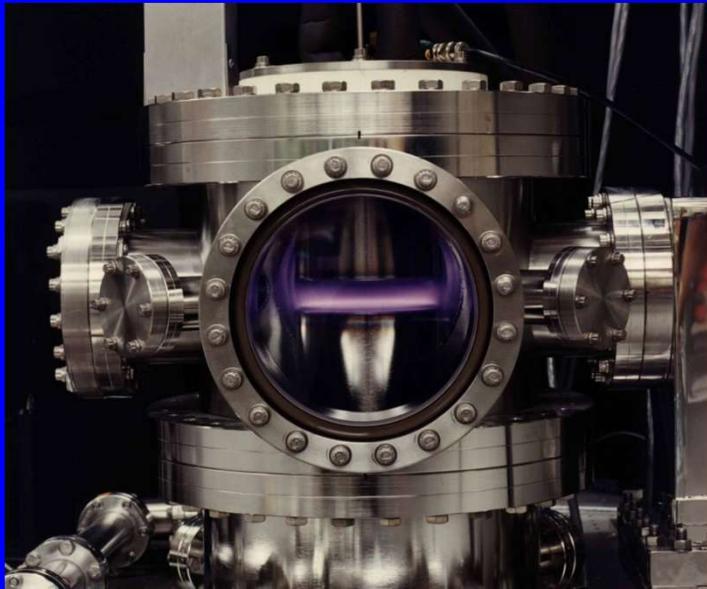


with radial gas flow



with inverse radial flow -
showerhead electrode

Construction of CCP reactors



GEC (Gaseous Electronics Conference) reference cell

Reactive Ion Etcher (RIE)
R.F. Diode

DPE MU Brno



UCP Processing Ltd.
(Balzers)

Principle of ICP discharges

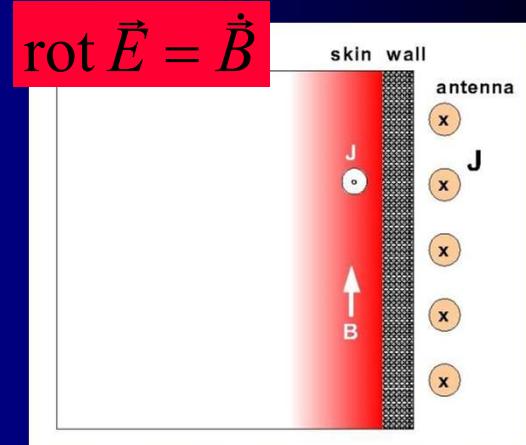
r.f. antenna in the form of coil attached to dielectric window – electromagnet creating rf mag field – induction of rf el field

Energy of electrical field is transferred to the electrons in thin „skin“ layer.

- non-collisional processes – electrons „collide“ with induced oscillating el. field
- energy is dissipated by collisional (ohmic) processes

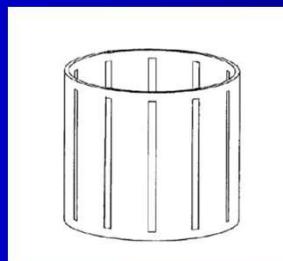
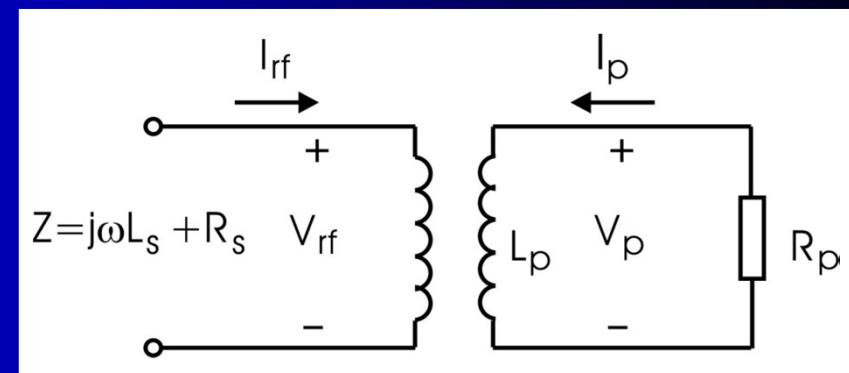
☞ non-capacitive coupling is a key point for low voltages (typically 20-30 V) in sheaths at electrodes and reactor walls

☞ Faraday shielding is used to suppress capacitive coupling (high voltage on the coil)



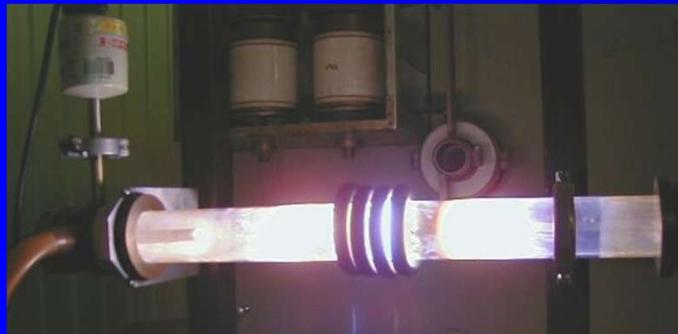
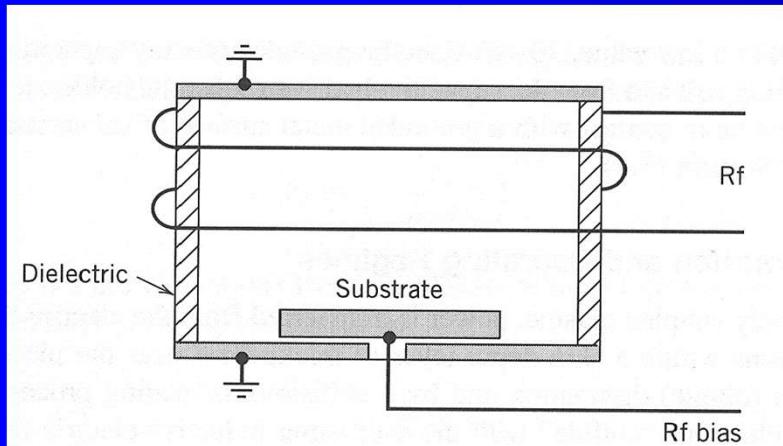
skin depth (collisionless)

$$\delta_s = \delta_c \equiv c / \omega_p$$

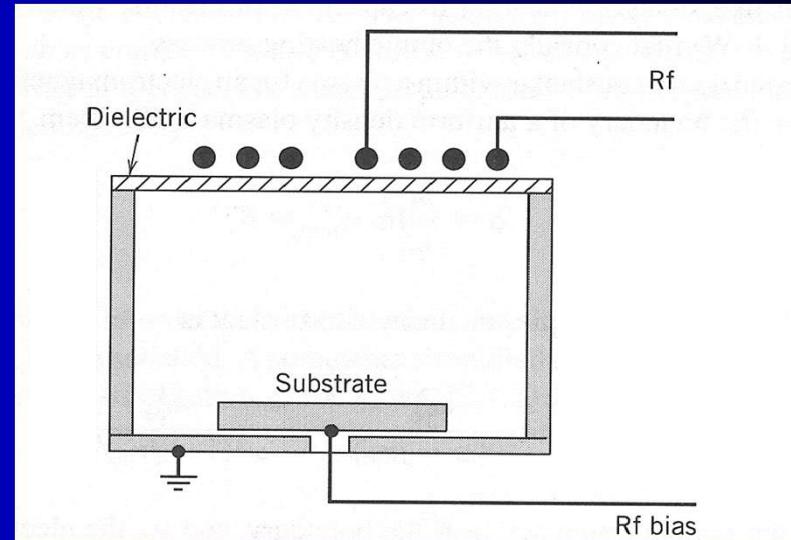


Construction of ICP reactors

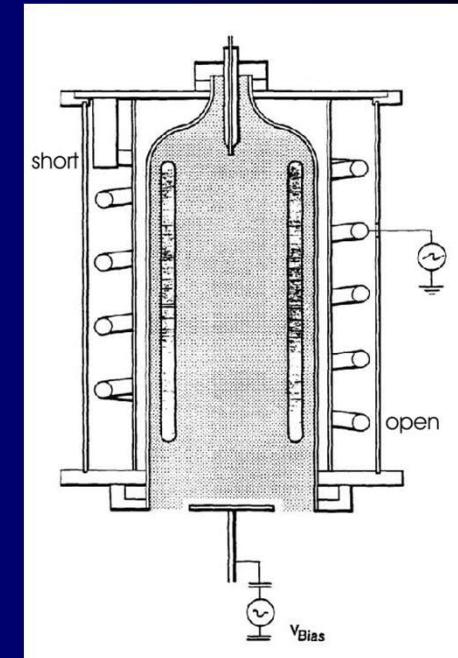
○ cylindrical geometry



○ planar geometry



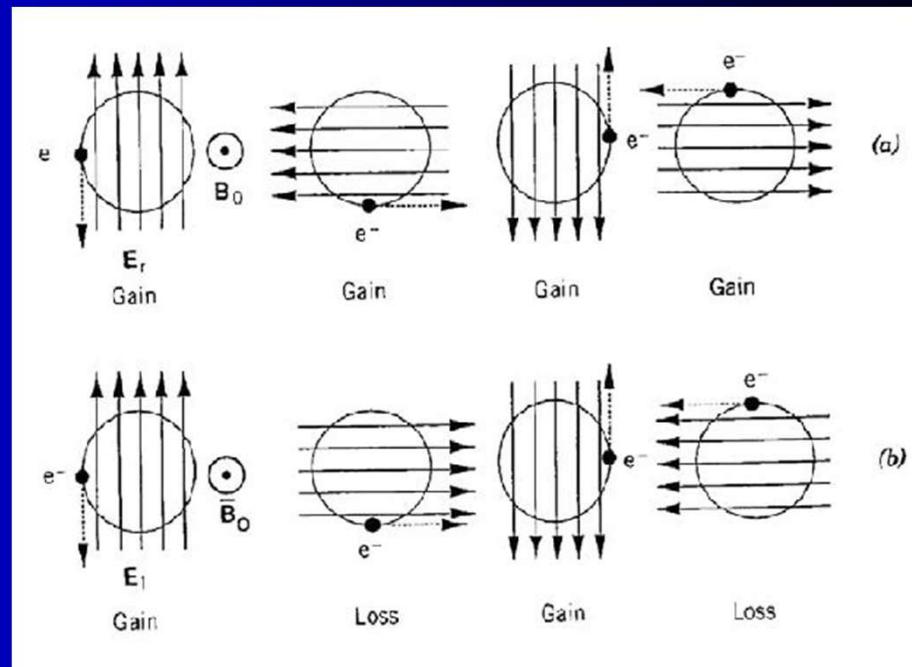
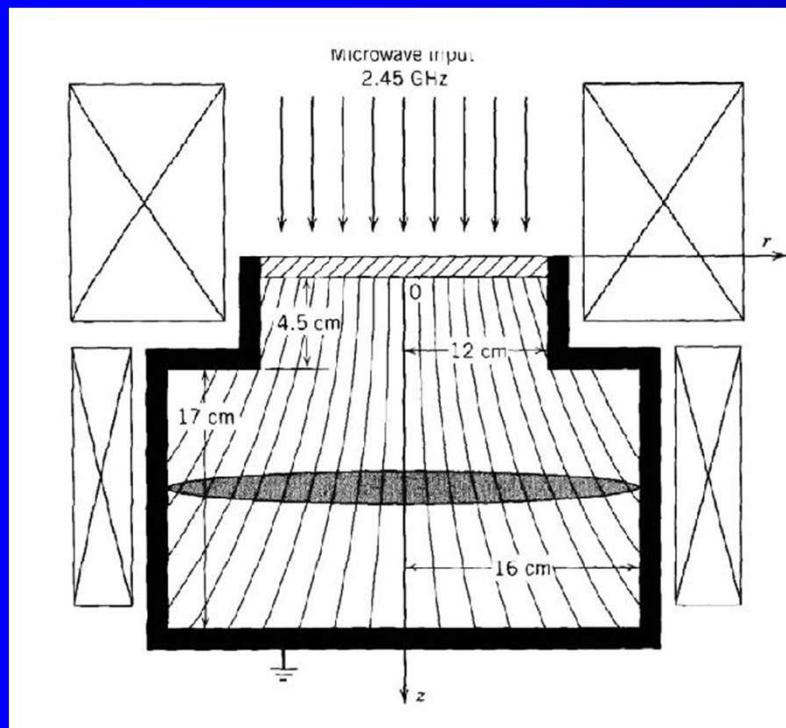
○ helical resonator



Principle of ECR discharges

elektrony rotují kolem siločár magnetického pole s elektronovou cyklotronovou frekvencí, která je v rezonanci s frekvencí elmag pole, a takto získávají energii

$$\omega = \omega_c = eB / m$$

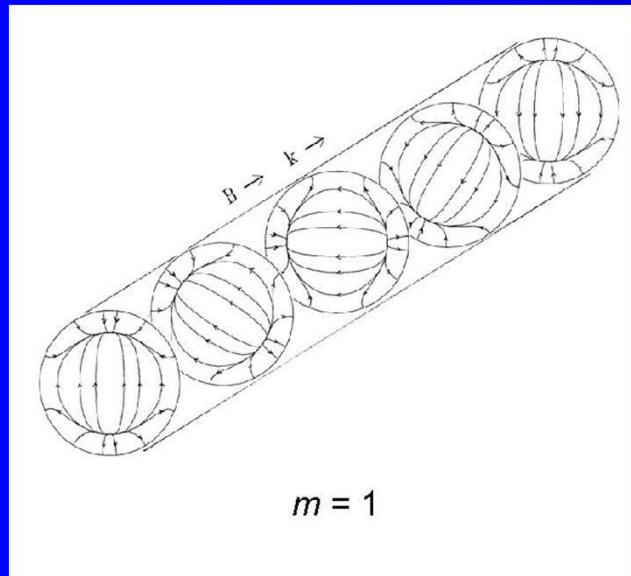


$$f = 2,45 \text{ GHz} \Leftrightarrow B = 875 \text{ G}$$

Princip helikonového výboje (helicon wave source)

Pomocí speciální rf antény (13,56 MHz) se generuje helikonová vlna, která postupuje podél vnějšího mg pole. Tato vlna způsobuje velmi efektivní ionizaci => vysoké hustoty plazmatu.

Mg pole má tři funkce (a) zvětšuje tloušťku skinové vrstvy, (b) pomáhá udržet delší dobu elektrony, (c) je dalším volným parametrem pro zlepšení uniformity hustoty



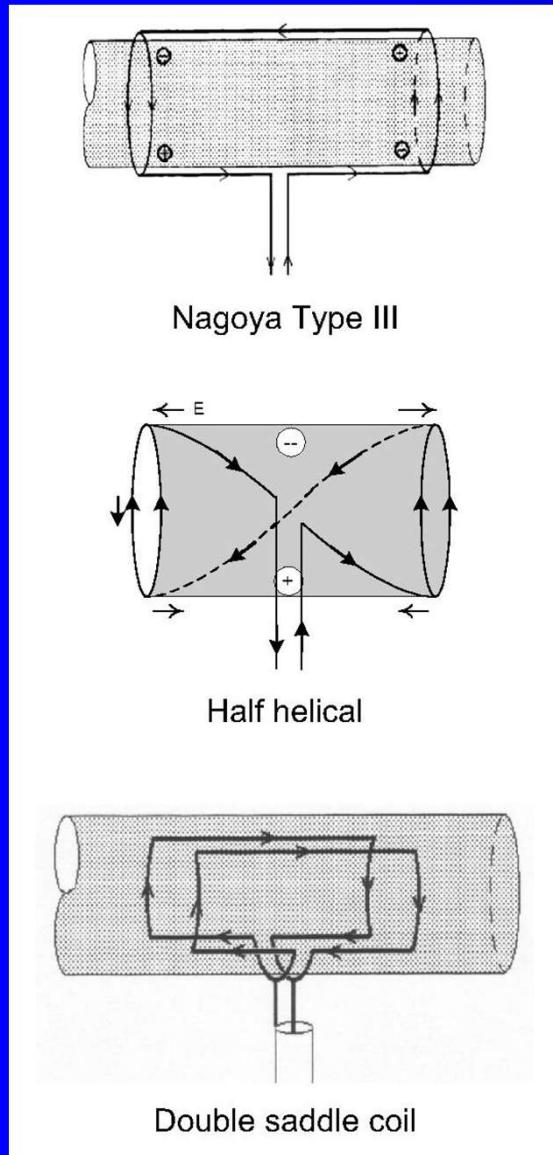
$$k = \frac{\omega}{k_z} \frac{\omega_p^2}{\omega_c c^2}$$

$$\cos \theta = k_z / k$$

θ je úhel mezi směrem šíření (vlnovým vektorem k) a vnějším mg. polem B_0

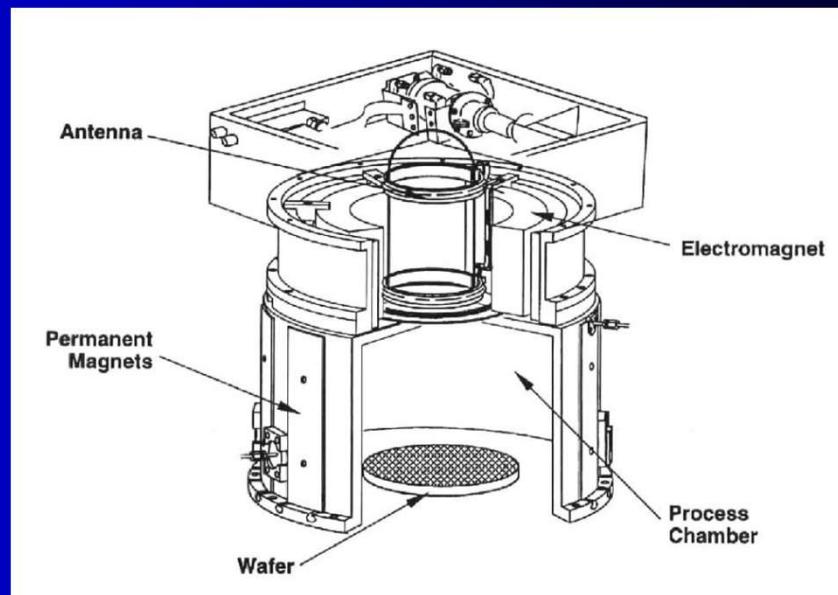
$$\vec{B} = \vec{B}(r) e^{i(m\theta + kz - \omega t)}$$

Konstrukce helikonových zdrojů



podle konstrukce
antény je možné generovat
určitý mód helikonové vlny

díky vysoké hustotě generovaného
plazmatu se používají v
„downstream“ konfiguraci



MORI PMT komerční zdroj

Comparison of (high f, low p) plasma sources

plasma source	frequency	density [cm ⁻³]	el. temper. [eV]	mg. field
CCP	r.f.	10 ⁹ -10 ¹¹	1-5	no
ICP	r.f.	10 ¹¹ -10 ¹² (≤ 10 ¹³)	2-7	optional
ECR	m.w.	10 ¹⁰ -10 ¹²	2-7	875 G
helicon	r.f.	10 ¹¹ -10 ¹² (10 ¹¹ -10 ¹⁴)	2-7	20-200 G